N-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

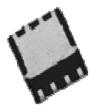
Typical Applications:

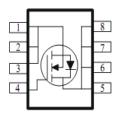
- DC/DC Conversion
- Power Routing
- Motor Drives

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I□ (A)		
30	2.8 @ V _{GS} = 10V	35		
30	$4.8 @ V_{GS} = 4.5V$	26		

DFN5X6-8L







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			30	V			
Gate-Source Voltage		V_{GS}	±20	V			
Continuous Drain Current ^a	T _A =25°C		35				
Continuous Drain Current	T _A =70°C	l _D	28	Α			
Pulsed Drain Current ^b		I _{DM}	120				
Continuous Source Current (Diode Conduction) a		I _S	7.3	Α			
Power Dissipation ^a	T _A =25°C		5	W			
Fower Dissipation	T _A =70°C	' D	3.2	VV			
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State		65	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

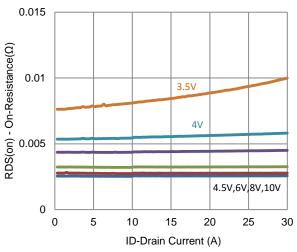
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uА	
Zero Gate Voltage Brain Gurrent	DSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	50			Α	
Drain-Source On-Resistance ^a	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			2.8	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 18 \text{ A}$			4.8	11122	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		82		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 3.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.75		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		35			
Gate-Source Charge	Q_gs	$I_D = 2 A$		10		nC	
Gate-Drain Charge	Q_gd	1D - 271		12			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 15 \text{ V}, R_1 = 7.5 \Omega,$		7			
Rise Time	t _r	$I_{DS} = 13 \text{ V}, \text{ NL} = 7.3 \Omega_{2},$ $I_{D} = 2 \text{ A},$		18		ne	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		95		ns	
Fall Time	t _f	VGEN = 10 V; NGEN 0 12		35			
Input Capacitance	C_{iss}			3671			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		449		pF	
Reverse Transfer Capacitance	C_{rss}			390			

Notes

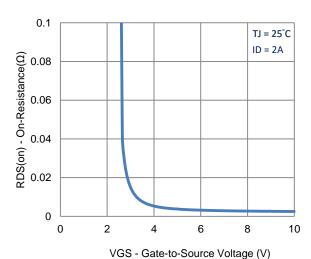
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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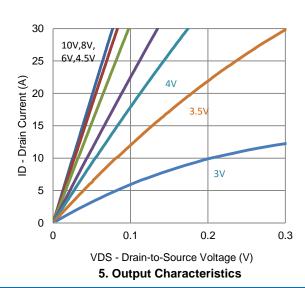
Typical Electrical Characteristics

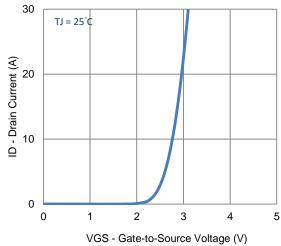


1. On-Resistance vs. Drain Current

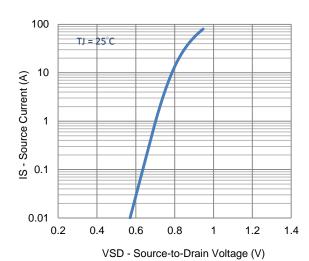


3. On-Resistance vs. Gate-to-Source Voltage

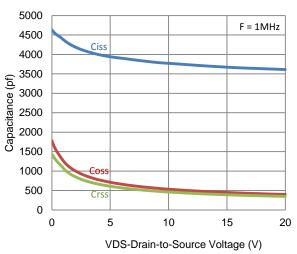




2. Transfer Characteristics

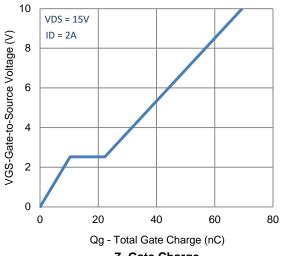


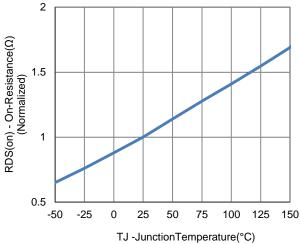
4. Drain-to-Source Forward Voltage



6. Capacitance

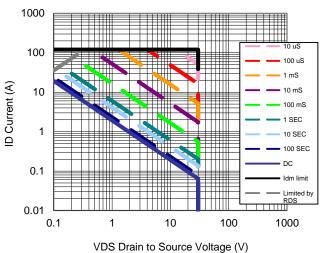
Typical Electrical Characteristics

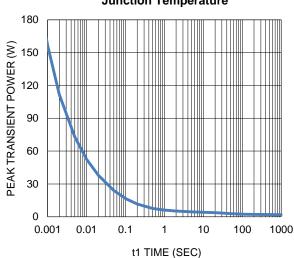




7. Gate Charge

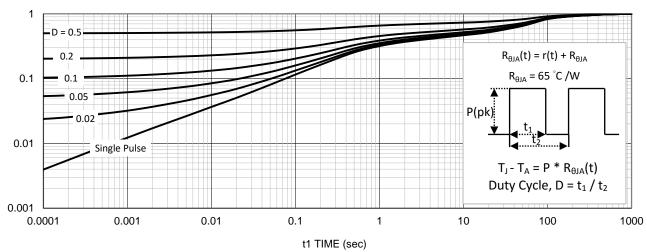






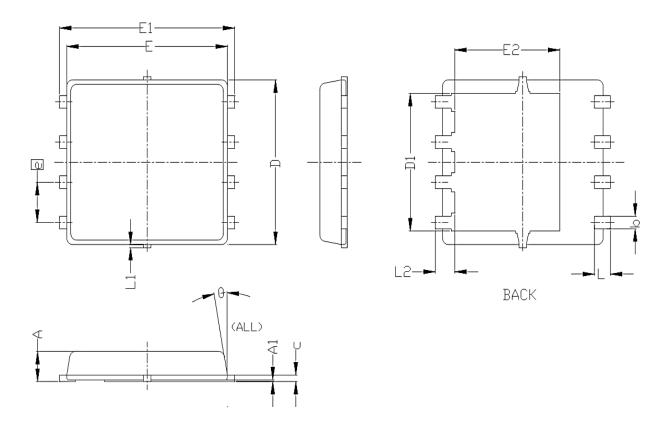
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS DIMENSIONS IN MILLIMETERS		DIMENSIONS IN INCHES					
SYMBULS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0.95	1.00	0.033	0.037	0.039	
A1	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0.15	0. 20	0. 25	0.006	0.008	0.010	
D		5. 20 BSC			0. 205 BSC		
D1	4. 35 BSC			0. 171 BSC			
Е	5, 55 BSC			0. 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0. 027 REF			
θ	0°		10°	0°		10°	